

ZXMS6003G

60V N-channel self protected enhancement mode IntelliFET™ MOSFET with programmable current limit

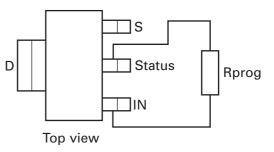
Summary

 $\begin{array}{lll} \mbox{Continuous drain source voltage} & \mbox{V_{DS} = 60V} \\ \mbox{On-state resistance} & \mbox{500m}\Omega \\ \mbox{Nominal load current (V_{IN} = 5V)} & \mbox{1.4A} \\ \mbox{Clamping energy} & \mbox{550mJ} \\ \end{array}$



Description

Self protected low side MOSFET. Monolithic over temperature, over current, over voltage (active clamp) and ESD protected logic level functionality. Intended as a general purpose switch, with status indication and programmable current limit.



Note: Rprog must be connected between the Status and IN pins

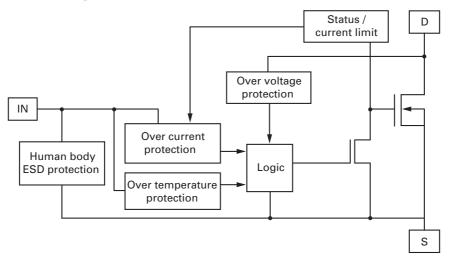
Features

- Current limit programmable via external resistor
- Status pin (analog status indication)
- Short circuit protection with auto restart
- Over voltage protection (active clamp)
- · Thermal shutdown with auto restart
- · Over-current protection
- Input Protection (ESD)
- Load dump protection (actively protects load)
- Logic Level Input
- · High continuous current rating

Ordering information

Device	Part mark	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMS6003GTA	ZXMS6003	7	12	1,000

Functional block diagram



Applications and information

- Especially suited for loads with a high in-rush current such as lamps and motors.
- All types of resistive, inductive and capacitive loads in switching applications.
- μ C compatible power switch for 12V and 24V DC applications.
- · Automotive rated.
- · Replaces electromechanical relays and discrete circuits.
- Linear mode capability the current-limiting protection circuitry is designed to de-activate at low V_{DS}, in order not to compromise the load current during normal operation. The design max. DC operating current is therefore determined by the thermal capability of the package/ board combination, rather than by the protection circuitry.

Note: This does not compromise the product's ability to self-protect during short-circuit load conditions.

- The current limit is programmable via an external resistor R_{prog} connected between Status and IN pins.
- Status pin voltage reflects the gate drive being applied internally to the power MOSFET.
 With V_{IN} = 5V and R_{prog} = 24kΩ:

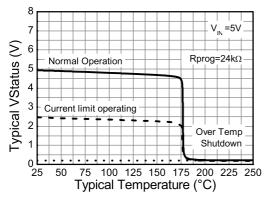
Status voltage ~ 5V indicates normal operation.

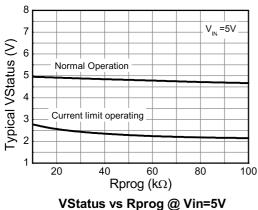
Status voltage ~ (2-3)V indicates that the device is in current-limiting mode.

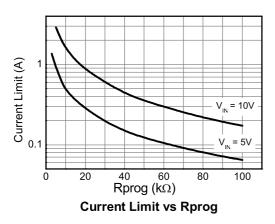
Status voltage < 1V indicates that the device is in thermal shutdown.

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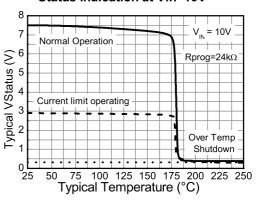
Current Limiting and Over Temp Shutdown Status Indication at Vin=5V

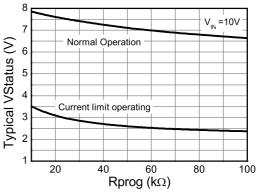




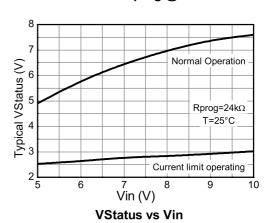


Current Limiting and Over Temp Shutdown Status Indication at Vin=10V





VStatus vs Rprog @ Vin=10V



Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Continuous drain-source voltage	V_{DS}	60	V
Drain-source voltage for short circuit protection V _{IN} =5V ^(a)	V _{DS(SC)}	36	V
Drain-source voltage for short circuit protection V _{IN} =10V ^(a)	V _{DS(SC)}	20	V
Continuous input voltage	V _{IN}	-0.2 +10	V
Peak input voltage	V _{IN}	-0.2 +20	V
Operating temperature range	T _j ,	-40 to +150	°C
Storage temperature range	T _{stg}	-55 to +150	°C
Power dissipation @ T _{amb} =25°C ^(a)	P_{D}	2.5	W
Continuous drain current @ V _{IN} =10V; T _{amb} =25°C ^(b)	I _D	1.6	Α
Continuous drain current @ V _{IN} =5V; T _{amb} =25°C ^(b)	I _D	1.4	Α
Continuous source current (body diode)(b)	I _S	3	Α
Pulsed source current (body diode)(c)	I _S	8	Α
Unclamped single pulse inductive energy	E _{AS}	550	mJ
Load dump protection	$V_{LoadDump}$	80	V
Electrostatic discharge (human body model)	V _{ESD}	4000	V
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		40/150/56	

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient	$R_{\Theta JA}$	50	°C/W
Junction to ambient	$R_{\Theta JA}$	28	°C/W

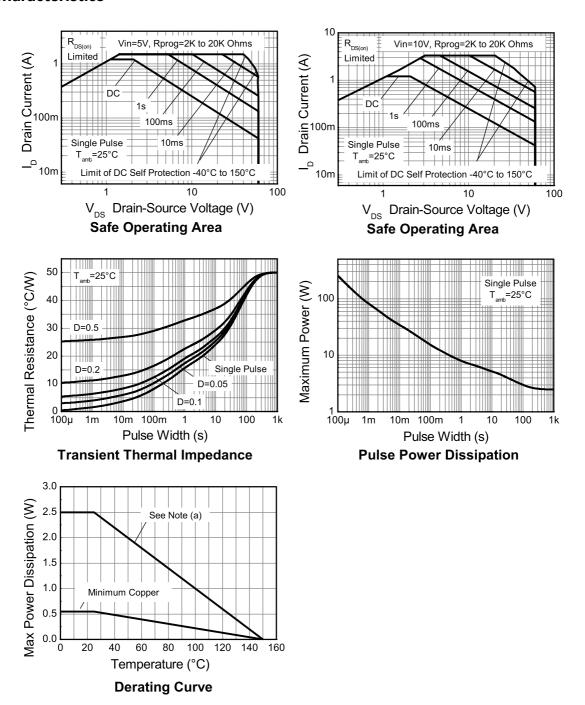
NOTES:

⁽a) For $I_{D(LIM)}$ < 1.2A (see safe operating area curve).

⁽b) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 board with a high coverage of single sided 2oz weight copper.

⁽c) For a device surface mounted on FR4 board and measured at t<=10s.

Characteristics



Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Static Characteristics	•	1		•		
Drain-source clamp voltage	V _{DS(AZ)}	60	70	75	V	I _D =10mA
Off state drain current	I _{DSS}		0.1	3	μΑ	V _{DS} =12V, V _{IN} =0V
Off state drain current	I _{DSS}		3	15	μΑ	V _{DS} =32V, V _{IN} =0V
Input threshold voltage (*)	V _{IN(th)}	1	2.1		V	V _{DS} =V _{GS} , I _D =1mA
Input current	I _{IN}		0.7	1.2	mA	V _{IN} =+5V
Input current	I _{IN}		1.5	2.7	mA	V _{IN} =+7V
Input current	I _{IN}		4	7	mA	V _{IN} =+10V
Static drain-source on-state resistance	R _{DS(on)}		520	675	mΩ	V _{IN} =5V, I _D =0.2A
Static drain-source on-state resistance	R _{DS(on)}		385	500	mΩ	V _{IN} =10V, I _D =0.5A
Current limit (†)	I _{D(LIM)}	0.2	0.3	0.4	А	V _{IN} =5V, Vds=10V Rprog=20k
Current limit ^(†)	I _{D(LIM)}	0.7	0.9	1.2	А	V _{IN} =10V, Vds=10V, Rprog=20k
Dynamic characteristics	•	1		•		
Turn-on time (V _{IN} to 90% I _D)	t _{on}		3.0	10	μS	Rprog=20k, R_L =22 Ω , V_{IN} =0 to 10V, V_{DD} =12V
Turn-off time (V _{IN} to 90% I _D)	t _{off}		13	20	μS	Rprog=20k, R_L =22 Ω , V_{IN} =10V to 0V, V_{DD} =12V
Slew rate on (70 to 50% V _{DD})	-dV _{DS} /dt _{on}		8	20	V/µs	Rprog=20k, R_L =22 Ω , V_{IN} =0 to 10V, V_{DD} =12V
Slew rate off (50 to 70% V _{DD})	DV _{DS} /dt _{on}		3.2	10	V/μs	Rprog=20k, R_L =22 Ω , V_{IN} =10V to 0V, V_{DD} =12V

NOTES:

^(*) Protection features may operate outside spec for $V_{\text{IN}}\!\!<\!4.5V$ (†) The drain current is limited to a reduced value when Vds exceeds a safe level.

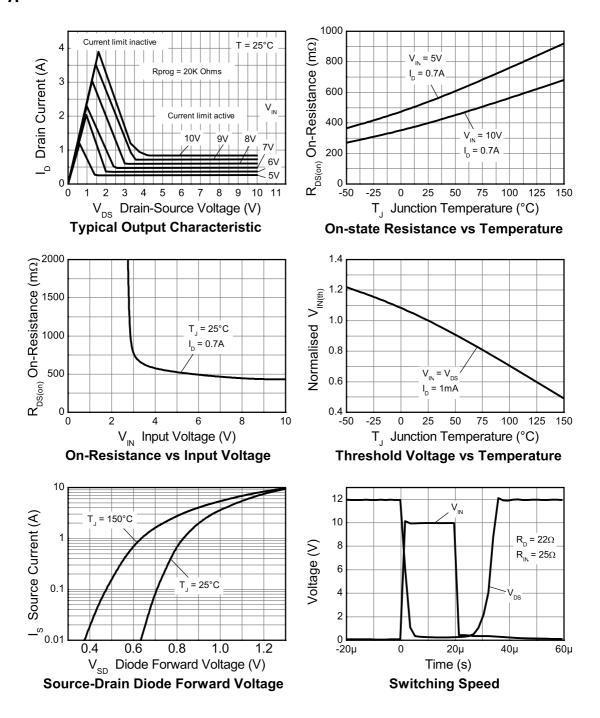
Electrical characteristics (at T_{amb} = 25°C unless otherwise stated) (cont.)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions	
Protection functions ^(‡)		•				•	
Required input voltage for over temperature protection	V _{PROT}	4.5			V		
Thermal overload trip temperature	T _{JT}	150	175		°C		
Thermal hysteresis			1		°C		
Unclamped single pulse inductive energy T _j =25°C	E _{AS}	550			mJ	I _{D(ISO})=0.7A, V _{DD} =32V	
Unclamped single pulse inductive energy T _j =150°C	E _{AS}	200			mJ	I _{D(ISO})=0.7A, V _{DD} =32V	
Status flag				l		1	
Normal operation	V _{STATUS}		4.95		V	V _{IN} = 5V	
Current limit operating	V _{STATUS}		2.5		V	V _{IN} = 5V	
Thermal shutdown activated	V _{STATUS}		0.2	1	V	V _{IN} = 5V	
Normal operation	V _{STATUS}		8.0		V	V _{IN} = 10V	
Current limit operation	V _{STATUS}		3.0		V	V _{IN} = 10V	
Thermal shutdown activated	V _{STATUS}		0.35	1	V	V _{IN} = 10V	
Inverse diode	ı		1	1		1	
Source drain voltage	V_{SD}			1	V	V _{IN} =0V, -I _D =1.4A	

NOTES:

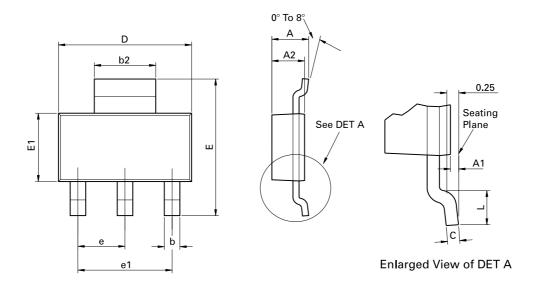
^(‡) Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.

Typical characteristics



ZXMS6003G

Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millin	neters	Inc	nches DIM Millimeters In		Millimeters		Inc	hes
	Min	Max	Min	Max		Min	Max	Min	Max
Α	-	1.80	-	0.071	е	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60	BSC	0.181	BSC
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
С	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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